

T-46-23-05



Integrated Device Technology, Inc.

CMOS STATIC RAM
64K (64K x 1-BIT)
IDT7187S
IDT7187L
FEATURES:

- High speed (equal access and cycle time)
 - Military: 20/25/35/45/55/70/85ns (max.)
 - Commercial: 15/20/25/35ns (max.)
- Low power consumption
 - IDT7187S
 - Active: 300mW (typ.)
 - Standby: 100μW (typ.)
 - IDT7187L
 - Active: 250mW (typ.)
 - Standby: 30μW (typ.)
- Battery backup operation—2V data retention (L version only)
- JEDEC standard high-density 22-pin plastic and hermetic DIP, 24-pin plastic SOIC, 22-pin and 28-pin leadless chip carrier and 24-pin CERPACK
- Produced with advanced CEMOS™ high-performance technology
- Separate data input and output
- Input and output directly TTL-compatible
- Military product compliant to MIL-STD-883, Class B
- Standard Military Drawing #5962-86015. Refer to Section 2/page 2-4

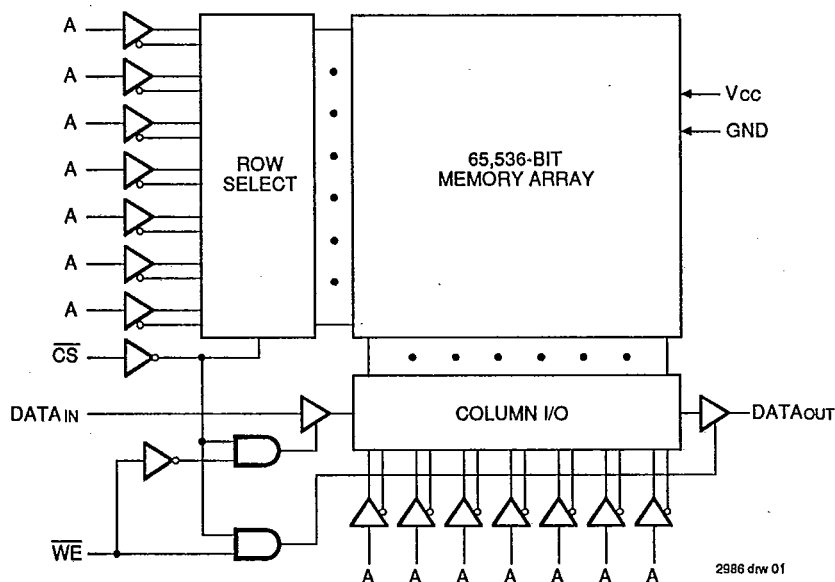
DESCRIPTION:

The IDT7187 is a 65,536-bit high-speed static RAM organized as 64K x 1. It is fabricated using IDT's high-performance, high-reliability technology, CEMOS. Access times as fast as 15ns are available with maximum power consumption of 700mW.

Both the standard (S) and low-power (L) versions of the IDT7187 provide two standby modes—LSB and LSB1. LSB provides low-power operation (358mW max.); LSB1 provides ultra-low-power operation (5mW max.). The low-power (L) version also provides the capability for data retention using battery backup. When using a 2V battery, the circuit typically consumes only 30μW.

Ease of system design is achieved by the IDT7187 with full asynchronous operation, along with matching access and cycle times. The device is packaged in an industry standard 22-pin, 300 mil plastic or hermetic DIP, 24-pin plastic SOIC (Gull-Wing and J-Bend), 22- and 28-pin leadless chip carriers, or 24-pin CERPACK.

Military grade product is manufactured in compliance with the latest revision of MIL-STD-883, Class B, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

FUNCTIONAL BLOCK DIAGRAM

CEMOS is a trademark of Integrated Device Technology, Inc.

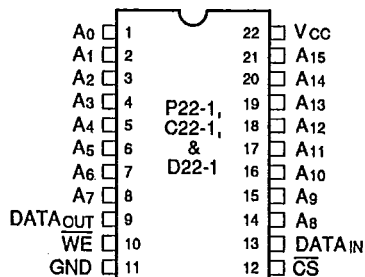
MILITARY AND COMMERCIAL TEMPERATURE RANGES**DECEMBER 1990**

IDT7187S/L
CMOS STATIC RAM 64K (64K x 1-BIT)

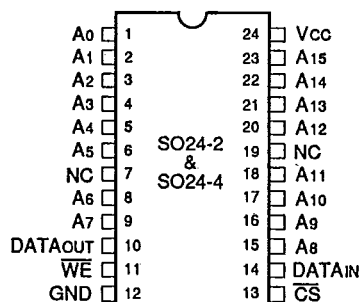
MILITARY AND COMMERCIAL TEMPERATURE RANGES

PIN CONFIGURATIONS

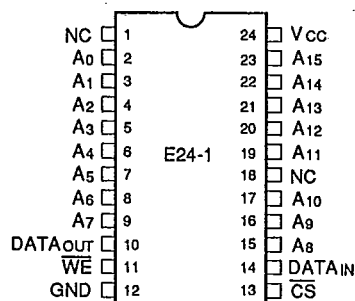
T-46-23-05



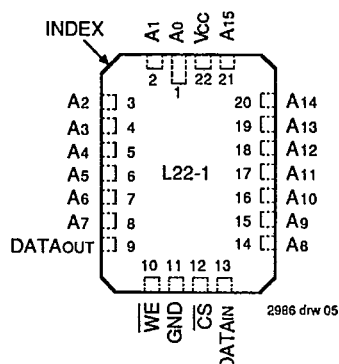
DIP
TOP VIEW



SOIC/SOJ
TOP VIEW



CERPACK
TOP VIEW



22-PIN LCC
TOP VIEW

PIN DESCRIPTIONS

Name	Description
A0-A15	Address Inputs
CS	Chip Select
WE	Write Enable
VCC	Power
DATAIN	Data Input
DATAOUT	Data Output
GND	Ground

2986 tdt 01

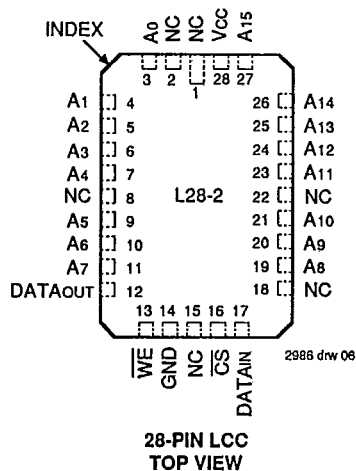
TRUTH TABLE⁽¹⁾

Mode	CS	WE	Output	Power
Standby	H	X	High Z	Standby
Read	L	H	DOU	Active

NOTES:

1. H = V_{IH}, L = V_{IL}, X = don't care.

2986 tdt 02



28-PIN LCC
TOP VIEW

IDT7187S/L
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MILITARY AND COMMERCIAL TEMPERATURE RANGES

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Com'l.	Mil.	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
TA	Operating Temperature	0 to +70	-55 to +125	°C
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
TSTG	Storage Temperature	-55 to +125	-65 to +150	°C
PT	Power Dissipation	1.0	1.0	W
IOUT	DC Output Current	50	50	mA

NOTE: 2986 tbl 03
1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

CAPACITANCE (TA = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
CIN	Input Capacitance	VIN = 0V	8	pF
COUT	Output Capacitance	VOUT = 0V	8	pF

NOTE: 2986 tbl 04
1. This parameter is determined by device characterization, but is not production tested.

RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
VCC	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
VIH	Input High Voltage	2.2	—	6.0	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾	—	0.8	V

NOTE: 2986 tbl 05
1. VIL (min.) = -3.0V for pulse width less than 20ns.

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade	Temperature	GND	VCC
Military	-55°C to +125°C	0V	5V ± 10%
Commercial	0°C to +70°C	0V	5V ± 10%

2986 tbl 06

DC ELECTRICAL CHARACTERISTICS

VCC = 5.0V ± 10%

Symbol	Parameter	Test Condition		IDT7187S		IDT7187L		Unit
				Min.	Max.	Min.	Max.	
ILI	Input Leakage Current	VCC = Max., VIN = GND to VCC	MIL. COM'L.	—	10	—	5	μA
ILO	Output Leakage Current	VCC = Max., CS = VIH, VOUT = GND to VCC	MIL. COM'L.	—	10	—	5	μA
VOL	Output Low Voltage	IOL = 10mA, VCC = Min.			0.5	—	0.5	V
		IOL = 8mA, VCC = Min.		—	0.4	—	0.4	
VOH	Output High Voltage	IOL = -4mA, VCC = Min.		2.4	—	2.4	—	V

2986 tbl 07

IDT7187S/L
CMOS STATIC RAM 64K (64K x 1-BIT)

MILITARY AND COMMERCIAL TEMPERATURE RANGES

DC ELECTRICAL CHARACTERISTICS⁽¹⁾

T-46-23-05

(VCC = 5V ± 10%, V_{LC} = 0.2V, V_{HC} = VCC - 0.2V)

Symbol	Parameter	Power	7187S15 ⁽³⁾		7187S20 7187L20		7187S25 7187L25		7187S35 7187L35		7187S45 7187L45		7187S55/70 7187L55/70		7187S85 7187L85		Unit
			Com'l.	Mil.	Com'l.	Mil. ⁽³⁾	Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	
I _{CC1}	Operating Power Supply Current CS = V _{IL} , Outputs Open VCC = Max., f = 0 ⁽²⁾	S	105	—	90	105	90	105	90	105	—	105	—	105	—	105	mA
		L	—	—	70	85	70	85	70	85	—	85	—	85	—	85	
I _{CC2}	Dynamic Operating Current CS = V _{IL} , Outputs Open VCC = Max., f = f _{MAX} ⁽²⁾	S	140	—	130	140	120	130	110	120	—	120	—	120	—	120	mA
		L	—	—	110	120	100	110	90	100	—	95	—	90	—	90	
I _{SB}	Standby Power Supply Current (TTL Level) CS ≥ V _{IH} , VCC = Max., Outputs Open, f = f _{MAX} ⁽²⁾	S	65	—	60	65	55	55	45	50	—	50	—	50	—	50	mA
		L	—	—	50	60	45	50	35	40	—	35	—	30/28	—	28	
I _{SB1}	Full Standby Power Supply Current (CMOS Level) CS ≥ V _{HC} , VCC = Max., V _{IN} ≥ V _{HC} or V _{IN} ≤ V _{LC} , f = 0 ⁽²⁾	S	20	—	15	20	15	20	15	20	—	20	—	20	—	20	mA
		L	—	—	0.3	1.5	0.3	1.5	0.3	1.5	—	1.5	—	1.5	—	1.5	

NOTES:

1. All values are maximum guaranteed values.
2. At f = f_{MAX} address and data inputs are cycling at the maximum frequency of read cycles of 1/t_{RC}. f = 0 means no input lines change.
3. These specs are preliminary.

2986 tbl 06

DATA RETENTION CHARACTERISTICS OVER ALL TEMPERATURE RANGES

(L Version Only) V_{HC} = VCC - 0.2V, V_{LC} = 0.2V

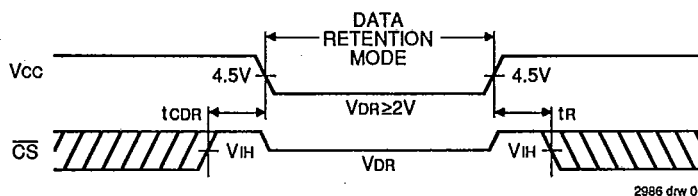
Symbol	Parameter	Test Condition	Min.	Typ. ⁽¹⁾ VCC @		Max. VCC @		Unit
				2.0V	3.0V	2.0V	3.0V	
V _{DR}	VCC for Data Retention	—	2.0	—	—	—	—	V
I _{CCDR}	Data Retention Current	MIL. COM'L.	— —	10 10	15 15	600 150	900 225	μA
t _{CDR} ⁽³⁾	Chip Deselect to Data Retention Time	CS ≥ V _{HC} V _{IN} ≥ V _{HC} or ≤ V _{LC}	0	—	—	—	—	ns
t _R ⁽³⁾	Operation Recovery Time	t _{RC} ⁽²⁾	—	—	—	—	—	ns
I _{LI} ⁽³⁾	Input Leakage Current	—	—	—	—	2	2	μA

NOTES:

1. TA = +25°C.
2. t_{RC} = Read Cycle Time.
3. This parameter is guaranteed, but not tested.

2986 tbl 09

LOW VCC DATA RETENTION WAVEFORM



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MILITARY AND COMMERCIAL TEMPERATURE RANGES

AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figures 1 and 2

2986 tbl 10

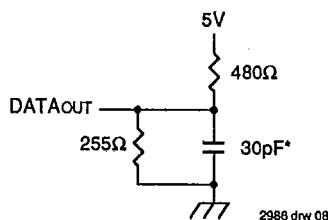


Figure 1. Output Load

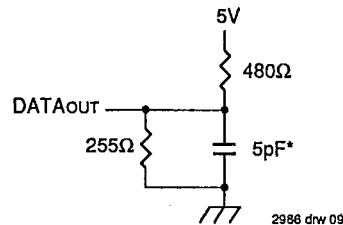


Figure 2. Output Load
(for tHZ, tLZ, tWZ and tOW)

*Includes scope and jig capacitances

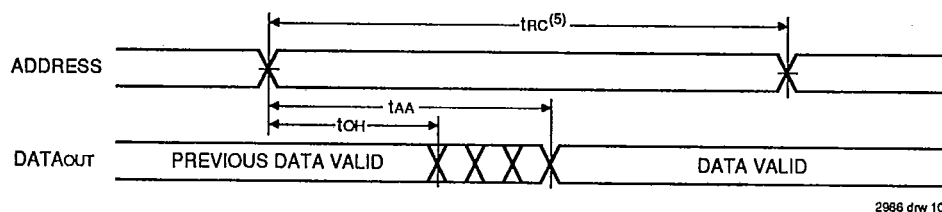
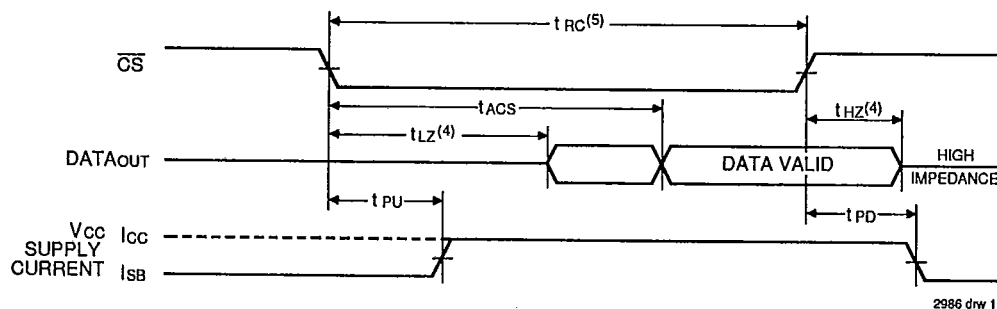
AC ELECTRICAL CHARACTERISTICS (VCC = 5.0V ± 10%, All Temperature Ranges)

Symbol	Parameter	7187S15 ⁽¹⁾ /20 7187L20		7187S25 7187L25		7187S35/45 ⁽²⁾ 7187L35/45 ⁽²⁾		7187S55 ⁽²⁾ 7187L55 ⁽²⁾		7187S70 ⁽²⁾ 7187L70 ⁽²⁾		7187S85 ⁽²⁾ 7187L85 ⁽²⁾		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle														
tRC	Read Cycle Time	15/20	—	25	—	35/45	—	55	—	70	—	85	—	ns
tAA	Address Access Time	—	15/20	—	25	—	35/45	—	55	—	70	—	85	ns
tACS	Chip Select Access Time	—	15/20	—	25	—	35/45	—	55	—	70	—	85	ns
tOH	Output Hold from Address Change	5	—	5	—	5	—	5	—	5	—	5	—	ns
tLZ	Output Selection to Output in Low Z ⁽³⁾	5	—	5	—	5	—	5	—	5	—	5	—	ns
tHZ	Chip Deselect to Output in High Z ⁽³⁾	—	6	—	12	—	17/20	—	30	—	30	—	40	ns
tPU	Chip Select to Power Up Time ⁽³⁾	0	—	0	—	0	—	0	—	0	—	0	—	ns
tPD	Chip Deselect to Power Down Time ⁽³⁾	—	15/20	—	20	—	30/35	—	35	—	35	—	40	ns

NOTES:

1. 0° to +70°C temperature range only.
2. -55°C to +125°C temperature range only.
3. This parameter guaranteed but not tested.

2986 tbl 11

TIMING WAVEFORM OF READ CYCLE NO. 1^(1,2)TIMING WAVEFORM OF READ CYCLE NO. 2^(1,3)

NOTES:

1. WE is high for read cycle.
2. CS is low for READ cycle.
3. Address valid prior to or coincident with CS transition low.
4. Transition is measured $\pm 200\text{mV}$ from steady state voltage with specified loading in Figure 2.
5. All READ cycle timings are referenced from the last valid address to the first transitioning address.

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CMOS STATIC RAM 64K (64K x 1-BIT)

MILITARY AND COMMERCIAL TEMPERATURE RANGES

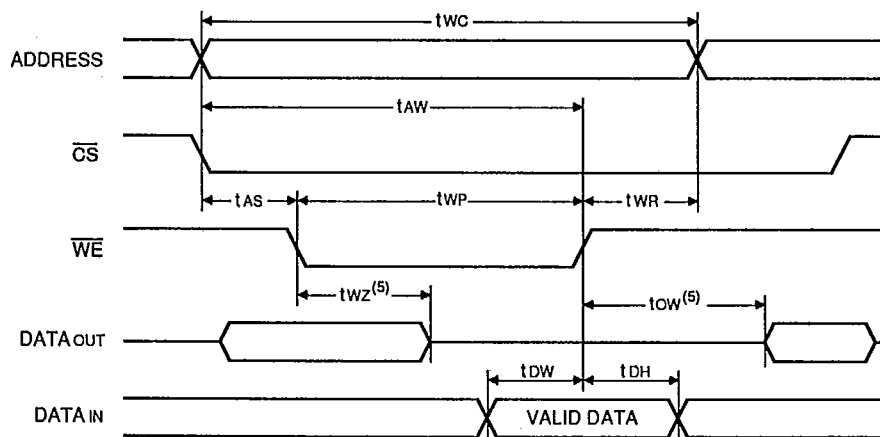
AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 5.0V \pm 10\%$, All Temperature Ranges)

Symbol	Parameter	7187S15 ⁽¹⁾ /20 7187L20		7187S25 7187L25		7187S35/45 ⁽²⁾ 7187L35/45 ⁽²⁾		7187S55 ⁽²⁾ 7187L55 ⁽²⁾		7187S70 ⁽²⁾ 7187L70 ⁽²⁾		7187S85 ⁽²⁾ 7187L85 ⁽²⁾		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Write Cycle														
tWC	Write Cycle Time	12/15	—	25	—	35/45	—	55	—	70	—	85	—	ns
tCW	Chip Select to End of Write	12/15	—	20	—	25/40	—	50	—	55	—	65	—	ns
tAW	Address Valid to End of Write	12/15	—	20	—	25/40	—	50	—	55	—	65	—	ns
tAS	Address Set-up Time	0	—	0	—	0	—	0	—	0	—	0	—	ns
tWP	Write Pulse Width	12/15	—	20	—	20/25	—	35	—	40	—	45	—	ns
tWR	Write Recovery Time	0	—	0	—	0	—	0	—	0	—	0	—	ns
tDW	Data Valid to End of Write	8/10	—	15	—	15/25	—	25	—	30	—	35	—	ns
tDH	Data Hold Time	0	—	5	—	5	—	5	—	5	—	5	—	ns
tWZ	Write Enable to Output in High Z ⁽³⁾	—	6/8	—	12	—	15/30	—	30	—	30	—	40	ns
tOW	Output Active from End of Write ⁽³⁾	0	—	0	—	0	—	0	—	0	—	0	—	ns

NOTES:

1. 0° to +70°C temperature range only.
2. -55°C to +125°C temperature range only.
3. This parameter guaranteed but not tested.

2988 tbt 12

TIMING WAVEFORM OF WRITE CYCLE NO. 1 ($\overline{WE}$ CONTROLLED TIMING)^(1,2,3,4)

2988 drw 12

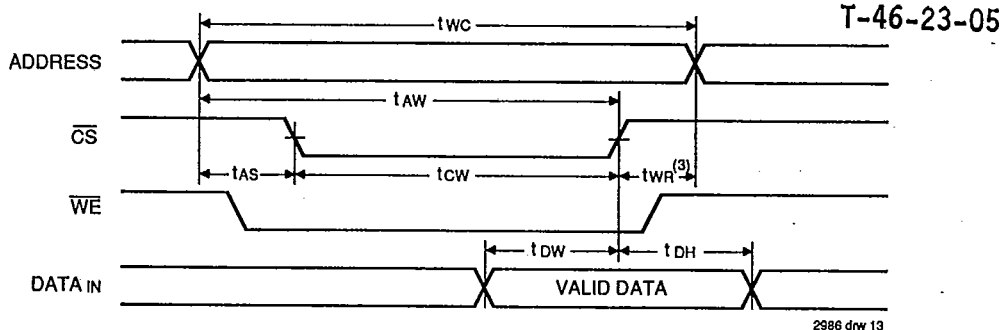
NOTES:

1. $\overline{WE}$ or $\overline{CS}$ must be high during all address transitions.
2. A write occurs during the overlap (t_{WP}) of a low $\overline{CS}$ and a low $\overline{WE}$.
3. t_{WR} is measured from the earlier of $\overline{CS}$ or $\overline{WE}$ going high to the end of the write cycle.
4. If the $\overline{CS}$ low transition occurs simultaneously with or after the $\overline{WE}$ low transition, the outputs remain in the high impedance state.
5. Transition is measured $\pm 200mV$ from steady state with a 5pF load (including scope and jig).

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MILITARY AND COMMERCIAL TEMPERATURE RANGES

TIMING WAVEFORM OF WRITE CYCLE NO. 2 ($\overline{CS}$ CONTROLLED TIMING)^(1,2,4,5)



NOTES:

1. $\overline{WE}$ or $\overline{CS}$ must be high during all address transitions.
2. A write occurs during the overlap (t_{WE}) of a low $\overline{CS}$ and a low $\overline{WE}$.
3. t_{WR} is measured from the earlier of $\overline{CS}$ or $\overline{WE}$ going high to the end of the write cycle.
4. If the $\overline{CS}$ low transition occurs simultaneously with or after the $\overline{WE}$ low transition, the outputs remain in the high impedance state.
5. Transition is measured $\pm 200\text{mV}$ from steady state with a 5pF load (including scope and jig).

ORDERING INFORMATION

IDT	XXXX	X	XXX	XX	X	
	Device Type	Power	Speed	Package	Process/ Temperature Range	
					Blank	Commercial (0°C to +70°C)
					B	Military (-55°C to +125°C) Compliant to MIL-STD-883, Class B
					C	Side Braze Dip (300 mil)
					D	Ceramic (300 mil)
					P	Plastic DIP (300 mil)
					L22	Leadless Chip Carrier (22 pins)
					SO	Small Outline IC (Gull-Wing)
					E	CERPACK
					Y	Small Outline (J-Bend)
					L28	Leadless Chip Carrier (28 pins)
					15	Commercial Only
					20	
					25	
					35	
					45	Military Only
					55	Military Only
					70	Military Only
					85	Military Only
					S	Standard Power
					L	Low Power
					7187	64K (64K x 1-Bit)

Speed in Nanoseconds

2986 drw 14